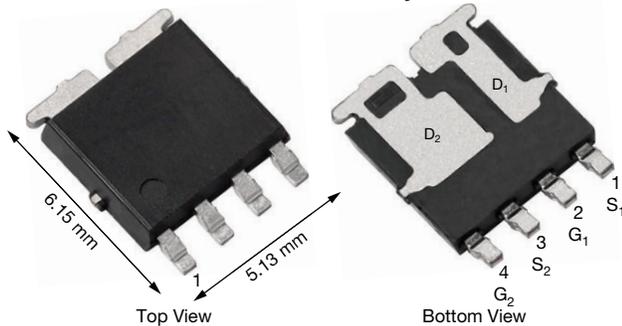


Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFETs

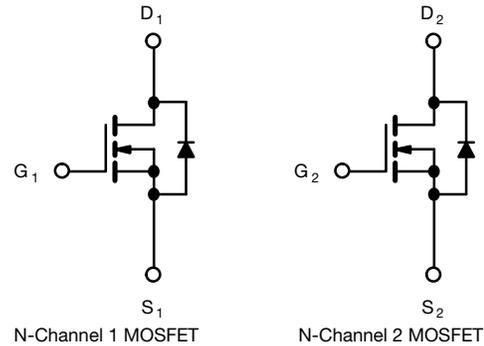
PowerPAK® SO-8L Dual Asymmetric

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V _{DS} (V)	60	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0355	0.0155
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.0480	0.0200
I _D (A)	15	40
Configuration	Dual N	
Package	PowerPAK SO-8L Dual Asymmetric	



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-source voltage	V _{DS}	60	60	V
Gate-source voltage	V _{GS}	± 20		
Continuous drain current	I _D	T _C = 25 °C	15 ^a	A
		T _C = 125 °C	11	
Continuous source current (diode conduction)	I _S	15 ^a	44	A
Pulsed drain current ^b	I _{DM}	30	70	
Single pulse avalanche current	I _{AS}	12	20	mJ
Single pulse avalanche energy	E _{AS}	7.2	20	
Maximum power dissipation ^b	P _D	T _C = 25 °C	27	W
		T _C = 125 °C	9	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175		°C
Soldering recommendations (peak temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-ambient	R _{thJA}	85	85	°C/W
Junction-to-case (drain)	R _{thJC}	5.5	3.1	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT	
Static									
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	60	-	-	V	
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	60	-	-		
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	1.5	2.0	2.5	V	
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	1.5	2.0	2.5		
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		N-Ch 1	-	-	± 100	nA	
				N-Ch 2	-	-	± 100		
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 1	-	-	1	μA	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 2	-	-	1		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	250		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	250		
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 1	10	-	-	A	
		$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 2	20	-	-		
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}$	N-Ch 1	-	0.0295	0.0355	Ω	
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}$	N-Ch 2	-	0.0126	0.0155		
		$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0563		
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0253		
		$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0700		
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0311		
		$V_{GS} = 4.5\text{ V}$	$I_D = 1\text{ A}$	N-Ch 1	-	0.0400	0.0480		
		$V_{GS} = 4.5\text{ V}$	$I_D = 3\text{ A}$	N-Ch 2	-	0.0165	0.0200		
Dynamic ^b									
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	410	550	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	967	1260		
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	212	280	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	436	570		
Reverse transfer capacitance	C_{rss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	15	20	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	18	25		
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	6.5	10	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	14.5	23		
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	1.4	-	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	2.7	-		
Gate-drain charge ^c	Q_{gd}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	0.9	-	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	2.1	-		
Gate resistance	R_g	$f = 1\text{ MHz}$			N-Ch 1	0.7	1.47	2.2	Ω
					N-Ch 2	0.3	0.62	0.95	



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Dynamic ^b							
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 30\ \Omega$, $I_D \equiv 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	9	15	ns
		$V_{DD} = 30\text{ V}$, $R_L = 15\ \Omega$, $I_D \equiv 2\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	13	20	
Rise time ^c	t_r	$V_{DD} = 30\text{ V}$, $R_L = 30\ \Omega$, $I_D \equiv 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	3	5	
		$V_{DD} = 30\text{ V}$, $R_L = 15\ \Omega$, $I_D \equiv 2\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	3	5	
Turn-off delay time ^c	$t_{d(off)}$	$V_{DD} = 30\text{ V}$, $R_L = 30\ \Omega$, $I_D \equiv 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	15	25	
		$V_{DD} = 30\text{ V}$, $R_L = 15\ \Omega$, $I_D \equiv 2\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	23	35	
Fall time ^c	t_f	$V_{DD} = 30\text{ V}$, $R_L = 30\ \Omega$, $I_D \equiv 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 1	-	10	15	
		$V_{DD} = 30\text{ V}$, $R_L = 15\ \Omega$, $I_D \equiv 2\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	N-Ch 2	-	10	15	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I_{SM}		N-Ch 1	-	-	30	A
			N-Ch 2	-	-	70	
Forward voltage	V_{SD}	$I_F = 2\text{ A}$, $V_{GS} = 0\text{ V}$	N-Ch 1	-	0.81	1.2	V
		$I_F = 5\text{ A}$, $V_{GS} = 0\text{ V}$	N-Ch 2	-	0.80	1.2	
Body diode reverse recovery time	t_{rr}	$I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	24	50	ns
		$I_F = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	36	75	
Body diode reverse recovery charge	Q_{rr}	$I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	17	35	nC
		$I_F = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	30	60	
Reverse recovery fall time	t_a	$I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	12	-	ns
		$I_F = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	19	-	
Reverse recovery rise time	t_b	$I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	12	-	
		$I_F = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	17	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$	$I_F = 2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 1	-	-1.3	-	A
		$I_F = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	N-Ch 2	-	-1.6	-	

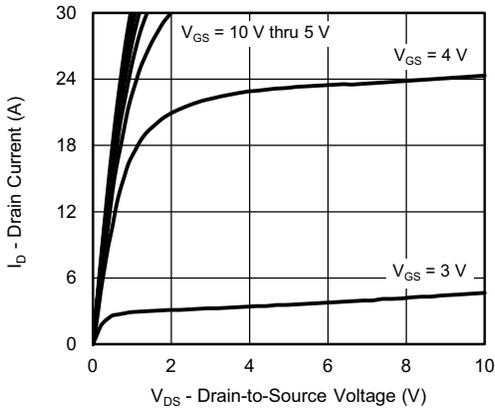
Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

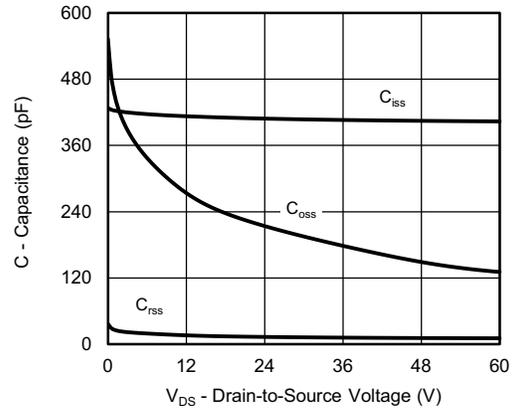
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



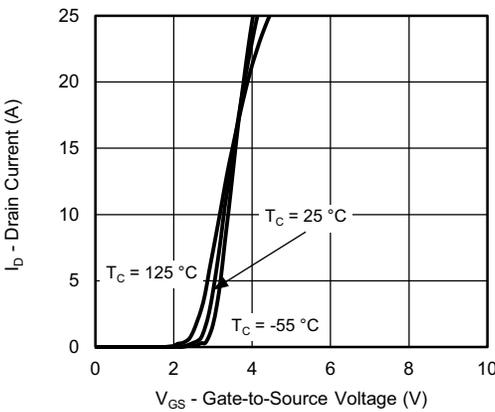
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



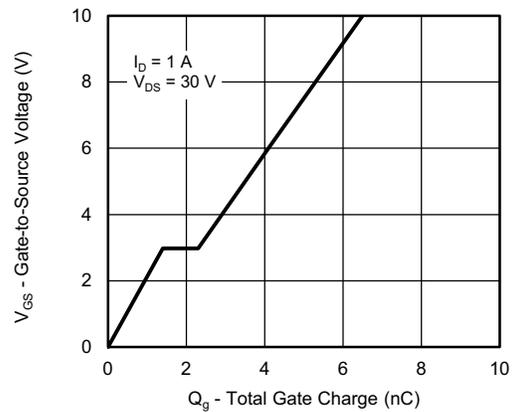
Output Characteristics



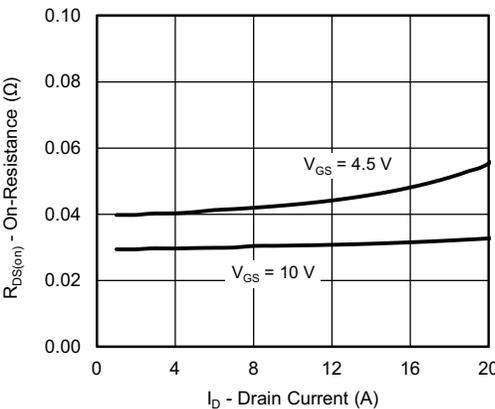
Capacitance



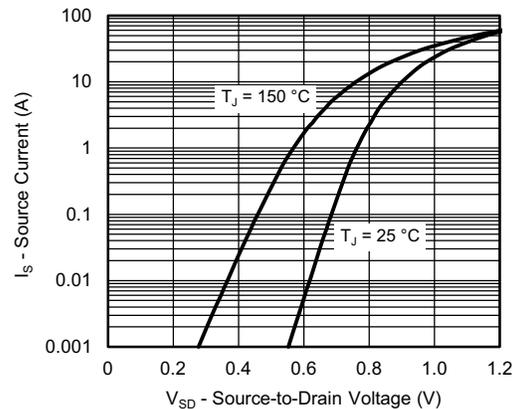
Transfer Characteristics



Gate Charge

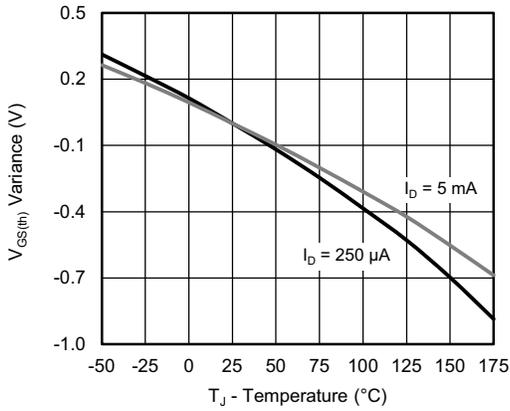


On-Resistance vs. Drain Current

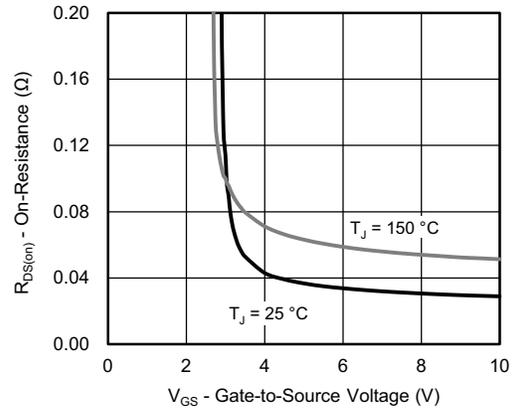


Source Drain Diode Forward Voltage

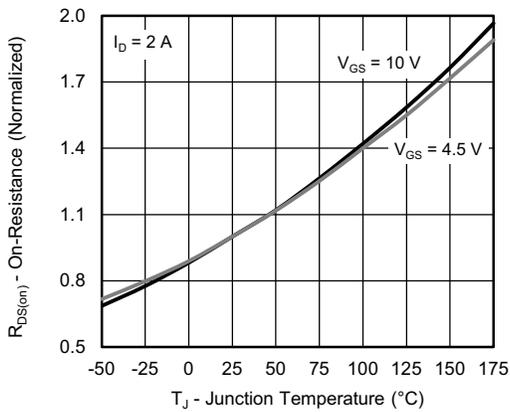
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



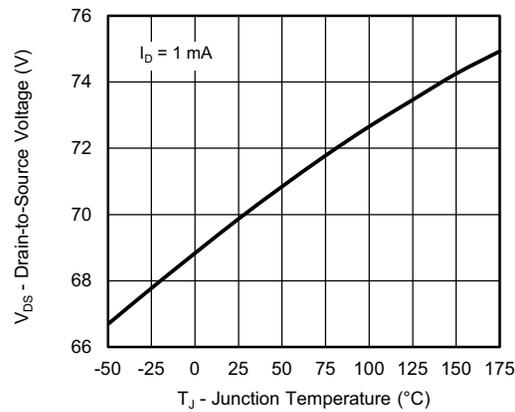
Threshold Voltage



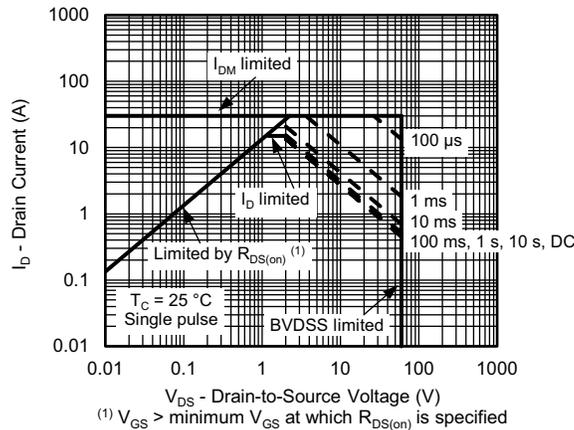
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature

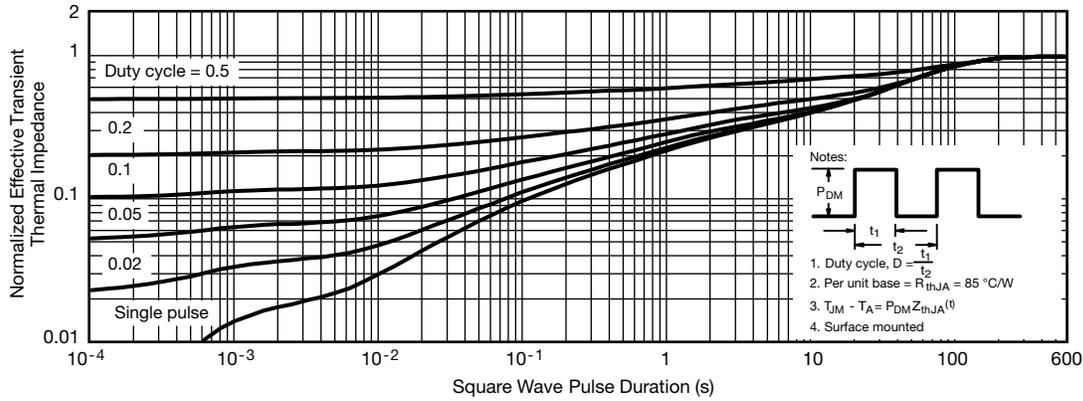


⁽¹⁾ $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

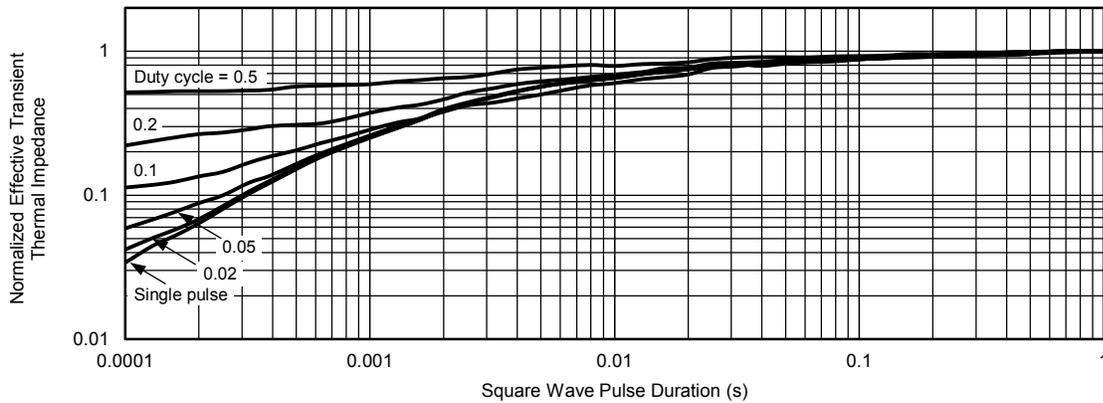
Safe Operating Area



N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

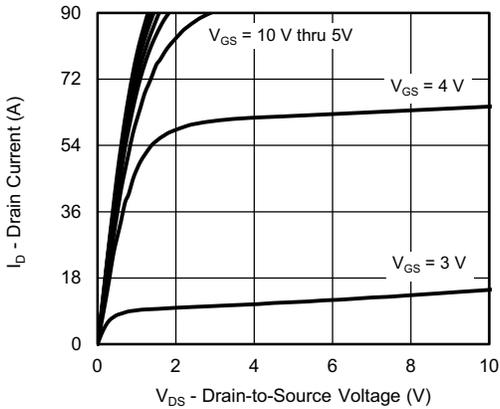


Normalized Thermal Transient Impedance, Junction-to-Case

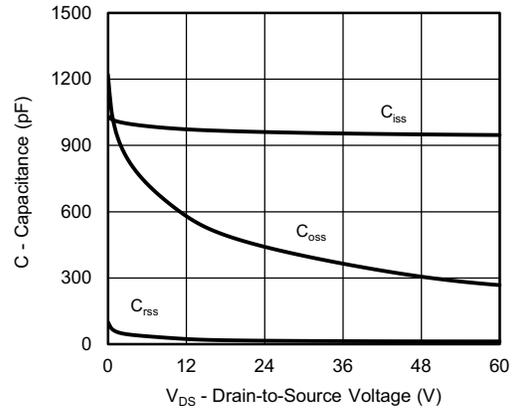
Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

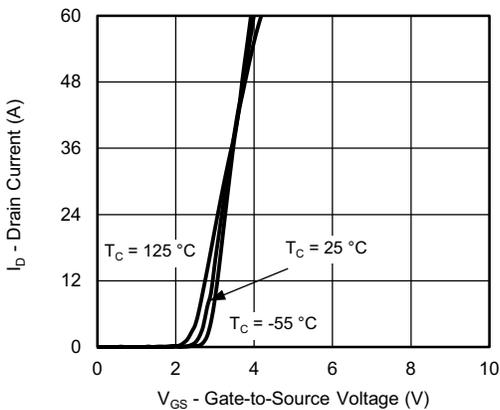
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



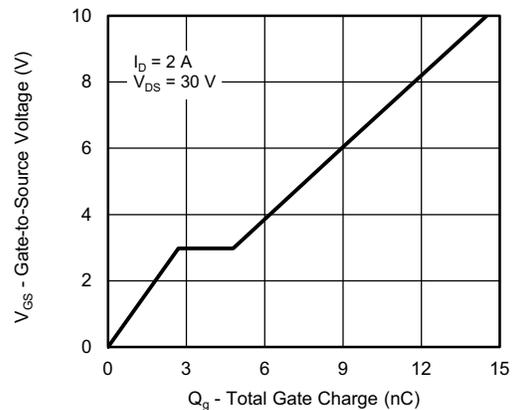
Output Characteristics



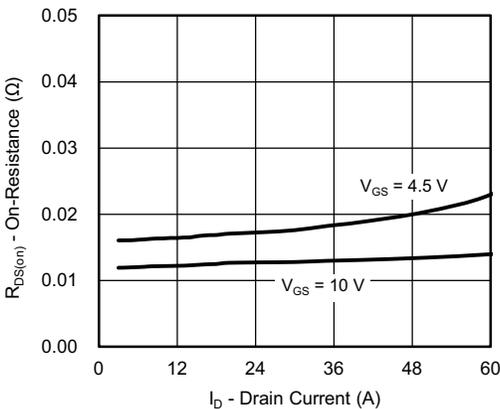
Capacitance



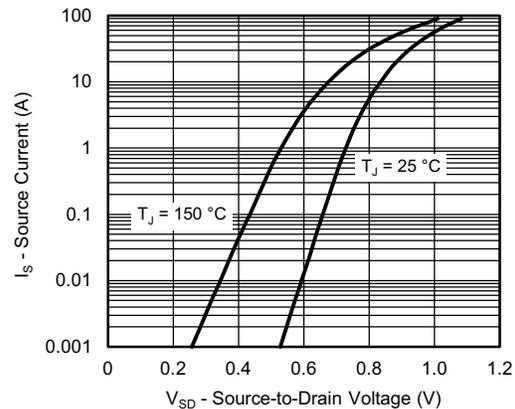
Transfer Characteristics



Gate Charge

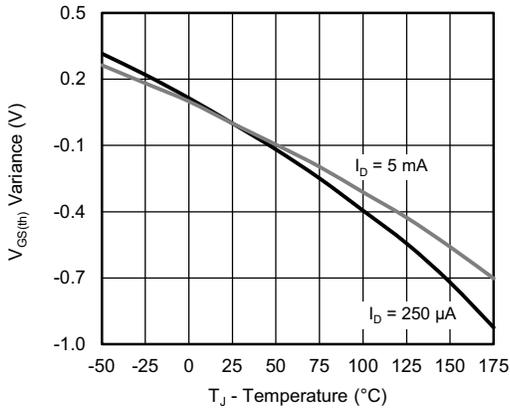


On-Resistance vs. Drain Current

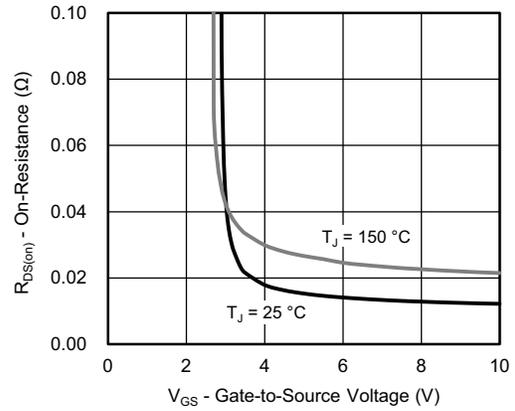


Source Drain Diode Forward Voltage

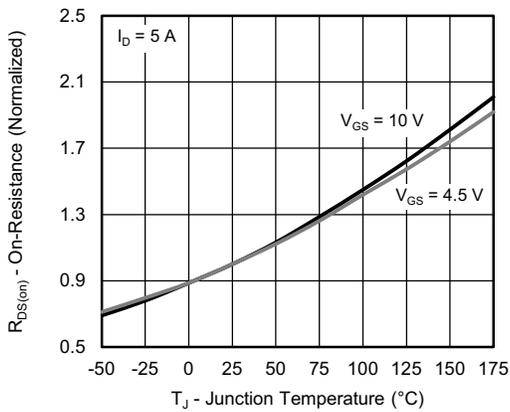
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



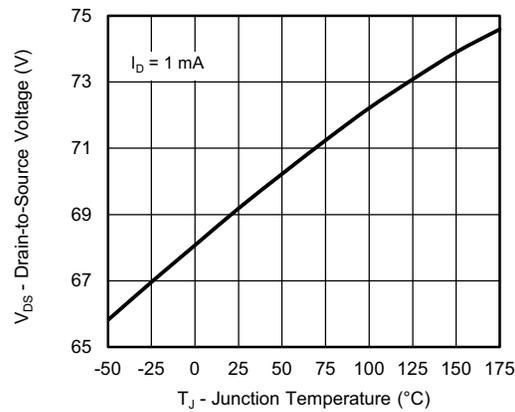
Threshold Voltage



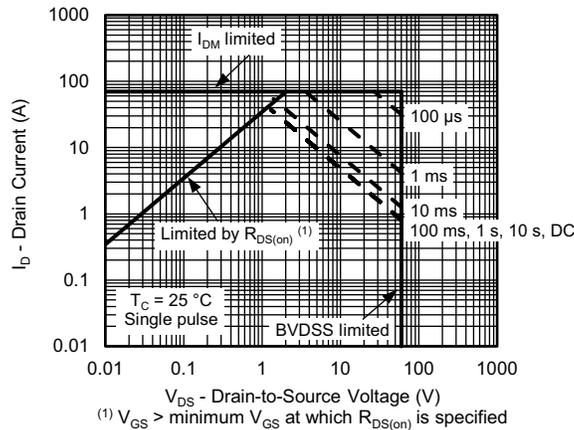
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature

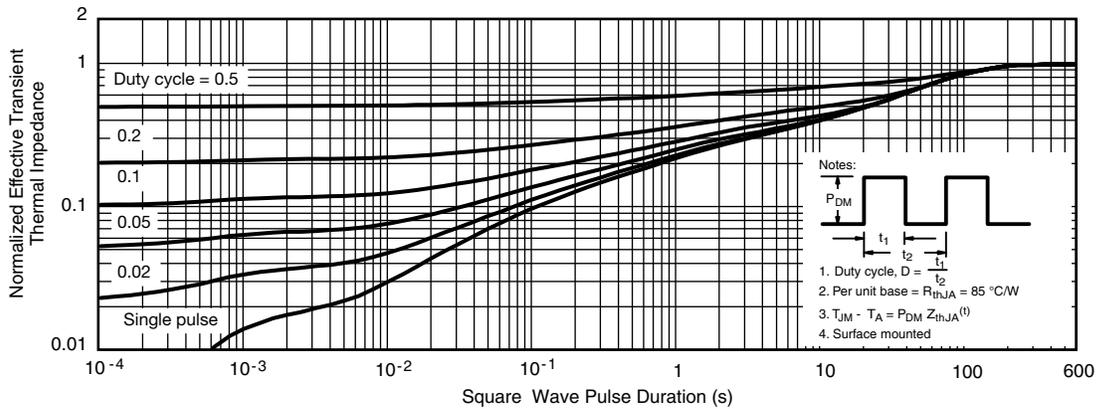


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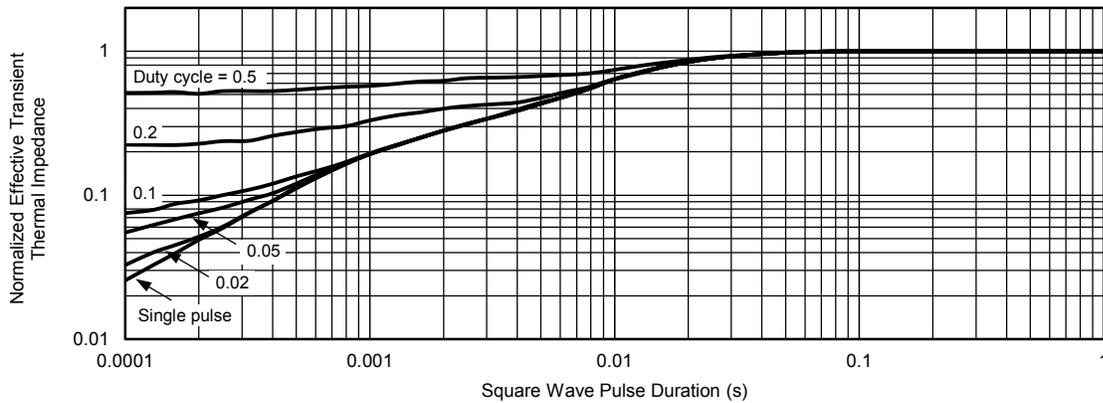
Safe Operating Area



N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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